

SSR1N50B / SSU1N50B

520V N-Channel MOSFET

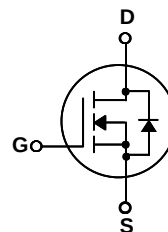
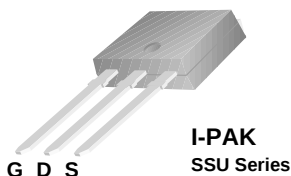
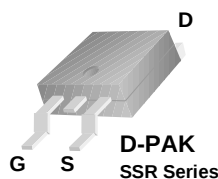
General Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switch mode power supplies, power factor correction and electronic lamp ballasts based on half bridge.

Features

- 1.3A, 520V, $R_{DS(on)} = 5.3\Omega$ @ $V_{GS} = 10V$
- Low gate charge (typical 8.3 nC)
- Low C_{rss} (typical 5.5 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	SSR1N50B / SSU1N50B	Units
V_{DSS}	Drain-Source Voltage	520	V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$)	1.3	A
	- Continuous ($T_C = 100^\circ\text{C}$)	0.82	A
I_{DM}	Drain Current - Pulsed (Note 1)	5.0	A
V_{GSS}	Gate-Source Voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	100	mJ
I_{AR}	Avalanche Current (Note 1)	1.3	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	2.6	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	5.5	V/ns
P_D	Power Dissipation ($T_A = 25^\circ\text{C}$) *	2.5	W
	Power Dissipation ($T_C = 25^\circ\text{C}$)	26	W
	- Derate above 25°C	0.21	W/ $^\circ\text{C}$
T_J, T_{stg}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	4.76	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient *	--	50	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	110	$^\circ\text{C/W}$

* When mounted on the minimum pad size recommended (PCB Mount)

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	520	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, Referenced to 25°C	--	0.54	--	V/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 520\text{ V}, V_{GS} = 0\text{ V}$	--	--	10	μA
		$V_{DS} = 400\text{ V}, T_C = 125^\circ\text{C}$	--	--	100	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.0	--	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 0.65\text{ A}$	--	4.1	5.3	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 40\text{ V}, I_D = 0.65\text{ A}$	--	1.65	--	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	260	340	pF
C_{oss}	Output Capacitance		--	25	33	pF
C_{rss}	Reverse Transfer Capacitance		--	5.5	7.2	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 250\text{ V}, I_D = 1.5\text{ A},$ $R_G = 25\text{ }\Omega$	--	14	40	ns
t_r	Turn-On Rise Time		--	40	90	ns
$t_{d(off)}$	Turn-Off Delay Time		--	35	80	ns
t_f	Turn-Off Fall Time		--	35	80	ns
Q_g	Total Gate Charge	$V_{DS} = 400\text{ V}, I_D = 1.5\text{ A},$ $V_{GS} = 10\text{ V}$	--	8.3	11	nC
Q_{gs}	Gate-Source Charge		--	1.5	--	nC
Q_{gd}	Gate-Drain Charge		--	3.4	--	nC

Drain-Source Diode Characteristics and Maximum Ratings

I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	1.3	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	5.0	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 1.3 A	--	--	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 1.5 A, dI _F / dt = 100 A/μs	--	230	--	ns
Q _{rr}	Reverse Recovery Charge		--	0.94	--	μC

Notes:

1. Repetitive Rating ; Pulse width limited by maximum junction temperature
2. $L = 106\text{ mH}$, $I_{AS} = 1.5\text{ A}$, $V_{DD} = 50\text{ V}$, $R_G = 25\text{ }\Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 1.5\text{ A}$, $dI/dt \leq 300\text{ A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$
5. Essentially independent of operating temperature

Typical Characteristics

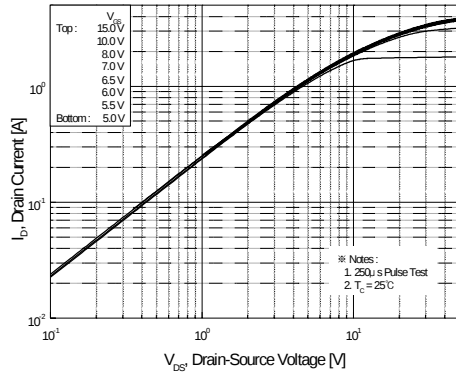


Figure 1. On-Region Characteristics

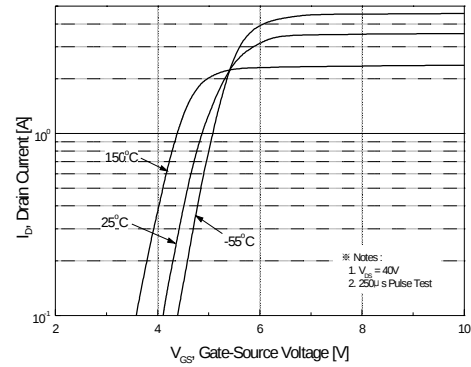


Figure 2. Transfer Characteristics

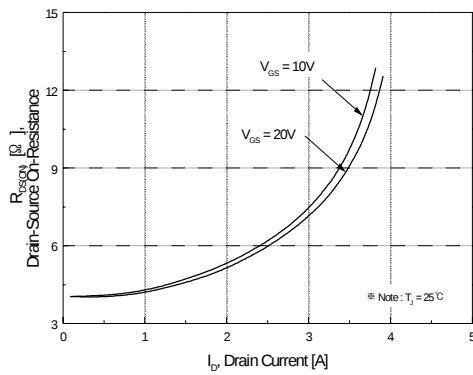


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

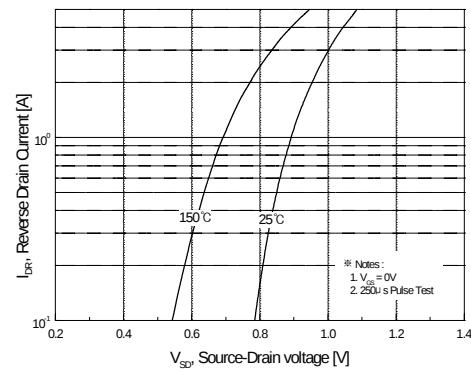


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

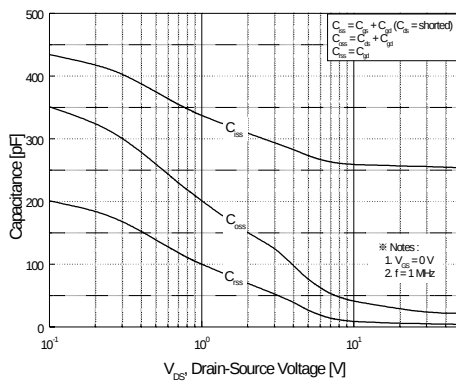


Figure 5. Capacitance Characteristics

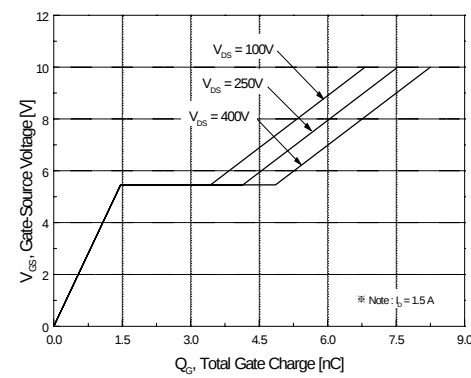


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

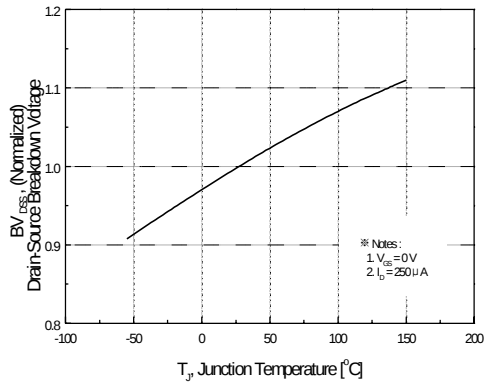


Figure 7. Breakdown Voltage Variation vs Temperature

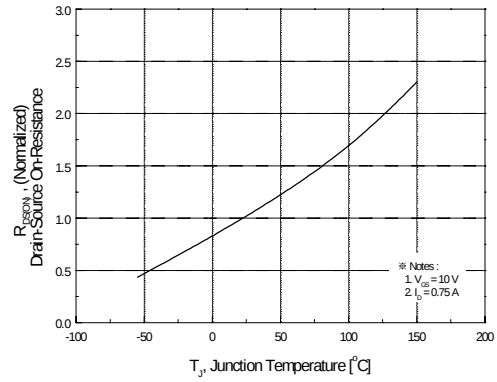


Figure 8. On-Resistance Variation vs Temperature

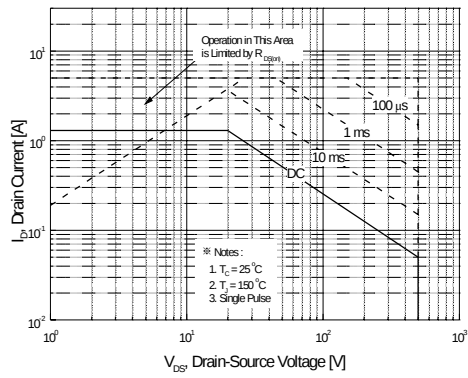


Figure 9. Maximum Safe Operating Area

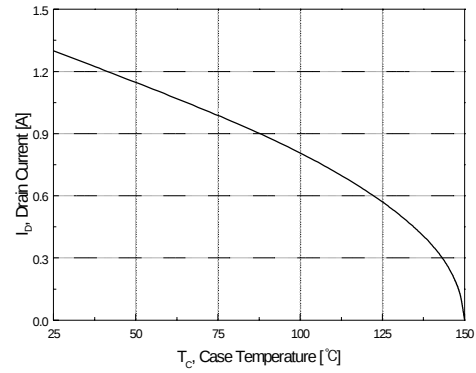


Figure 10. Maximum Drain Current vs Case Temperature

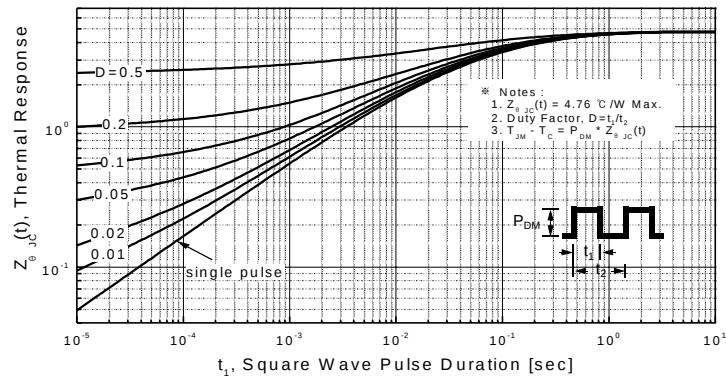
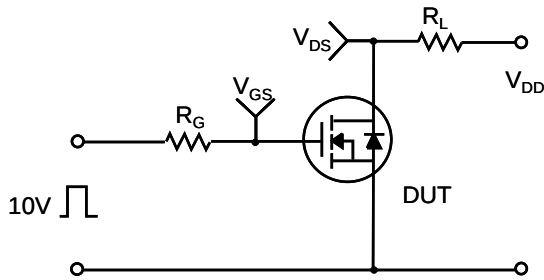


Figure 11. Transient Thermal Response Curve

Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms



Peak Diode Recovery dv/dt Test Circuit & Waveforms



Technical drawing of a 10-pin D-subminiature connector. The drawing includes three views: a front view, a side view, and a top view. Dimensions are provided in millimeters with tolerances.

Front View Dimensions:

- Overall width: 6.60 ± 0.20
- Pin pitch (center-to-center): 2.30 TYP [2.30 ± 0.20]
- Pin width: 0.76 ± 0.10
- Pin height: 0.80 ± 0.20
- Shell height: 0.60 ± 0.20
- Shell width (excluding pins): 5.34 ± 0.30
- Shell width (including pins): 6.10 ± 0.20
- Overall height: 9.50 ± 0.30
- Pin spacing (from centerline): (0.50) and (4.34)

Side View Dimensions:

- Shell height: 0.91 ± 0.10
- Pin height: 0.89 ± 0.10
- Pin width: 0.50 ± 0.10
- Pin spacing (from centerline): 0.50 ± 0.10
- Overall width: 2.30 ± 0.20
- Minimum shell thickness: $\text{MIN} 0.55$

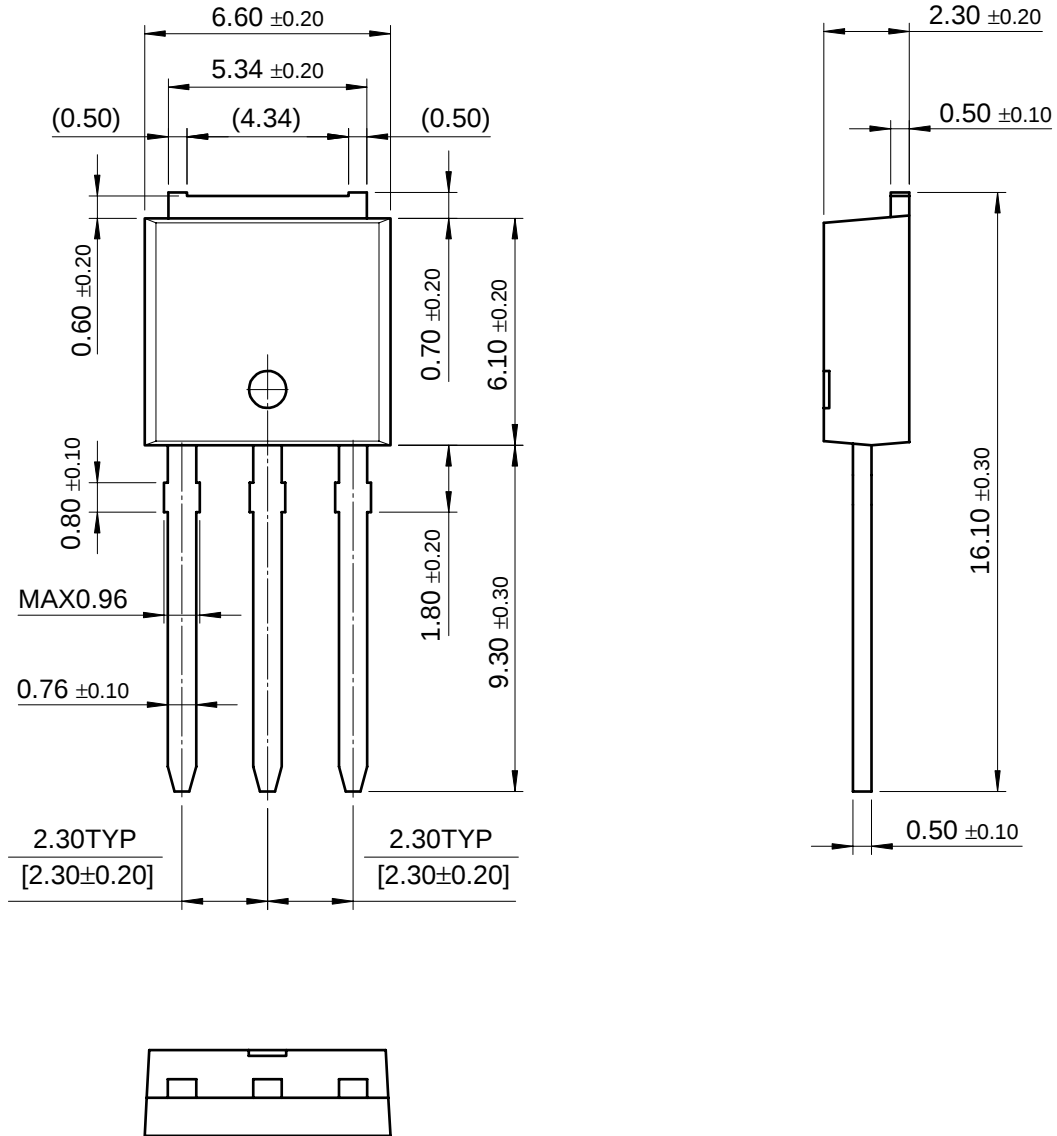
Top View Dimensions:

- Overall width: 6.60 ± 0.20
- Pin pitch (center-to-center): 2.30 TYP [2.30 ± 0.20]
- Pin width: 0.76 ± 0.10
- Pin height: 0.80 ± 0.20
- Shell height: 0.60 ± 0.20
- Shell width (excluding pins): 5.34 ± 0.30
- Shell width (including pins): 6.10 ± 0.20
- Overall height: 9.50 ± 0.30
- Pin spacing (from centerline): (0.50) and (4.34)

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Package Dimensions (Continued)

I-PAK



Dimensions in Millimeters

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